



Shantou Huashan Electronic Devices Co.,Ltd.

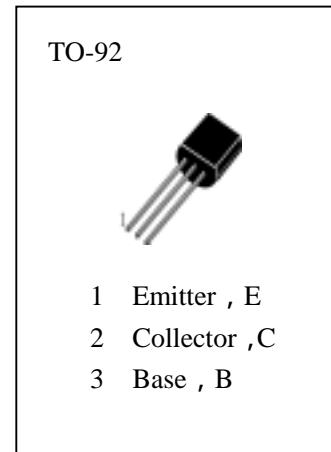
PNP SILICON TRANSISTOR

**H928S**

## AUDIO POWER AMPLIFIER APPLICATIONS

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$ —Storage Temperature.....	-55~150
$T_j$ —Junction Temperature.....	150
$P_C$ —Collector Dissipation.....	-750mW
$V_{CBO}$ —Collector-Base Voltage.....	-30V
$V_{CEO}$ —Collector-Emitter Voltage.....	-30V
$V_{EBO}$ —Emitter-Base Voltage.....	-5V
$I_C$ —Collector Current.....	-2A



### ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CBO}$	Collector-Base Breakdown Voltage	-30			V	$I_C=-100 \mu A, I_E=0$
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	-30			V	$I_C=-10mA, I_B=0$
$BV_{EBO}$	Emitter-Base Breakdown Voltage	5			V	$I_E=-1mA, I_C=0$
$I_{CBO}$	Collector Cut-off Current			-100	nA	$V_{CB}=-30V, I_E=0$
$I_{EBO}$	Emitter-Base Cut-off Current			-100	nA	$V_{EB}=-5V, I_C=0$
$HFE$	DC Current Gain	100		320		$V_{CE}=-2V, I_C=-500mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-2	V	$I_C=-1.5mA, I_B=-30mA$
$V_{BE(ON)}$	Base-Emitter On Voltage			-1	V	$V_{CE}=-2V, I_C=-500mA$
$f_T$	Current Gain-Bandwidth Product		120		MHz	$V_{CE}=-2V, I_C=-500mA$
$C_{ob}$	Collector-Base Capacitance		48		pF	$V_{CB}=-10V, I_E=0, f=1MHz$

### $hFE$ Classification

O

Y

100—200

160—320